



# 2SK4067 — N-Channel Silicon MOSFET

## General-Purpose Switching Device Applications

### Features

- Motor drive applications.
- 4.5V drive.

### Specifications

#### Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V <sub>DSS</sub>		30	V
Gate-to-Source Voltage	V <sub>GSS</sub>		±20	V
Drain Current (DC)	I <sub>D</sub>		8	A
Drain Current (Pulse)	I <sub>DP</sub>	PW≤10μs, duty cycle≤1%	32	A
Allowable Power Dissipation	P <sub>D</sub>		1	W
		T <sub>c</sub> =25°C	10	W
Channel Temperature	T <sub>ch</sub>		150	°C
Storage Temperature	T <sub>stg</sub>		-55 to +150	°C

#### Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> =1mA, V <sub>GS</sub> =0V	30			V
Zero-Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V			1	μA
Gate-to-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±16V, V <sub>DS</sub> =0V			±10	μA
Cutoff Voltage	V <sub>GS(off)</sub>	V <sub>DS</sub> =10V, I <sub>D</sub> =1mA	1.5		2.5	V
Forward Transfer Admittance	y <sub>fs</sub>	V <sub>DS</sub> =10V, I <sub>D</sub> =4A	2.6	4.4		S
Static Drain-to-Source On-State Resistance	R <sub>DS(on)1</sub>	I <sub>D</sub> =8A, V <sub>GS</sub> =10V		85	115	mΩ
	R <sub>DS(on)2</sub>	I <sub>D</sub> =4A, V <sub>GS</sub> =4.5V		155	220	mΩ
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =10V, f=1MHz		260		pF
Output Capacitance	C <sub>oss</sub>	V <sub>DS</sub> =10V, f=1MHz		65		pF
Reverse Transfer Capacitance	C <sub>rss</sub>	V <sub>DS</sub> =10V, f=1MHz		40		pF

Marking : K4067

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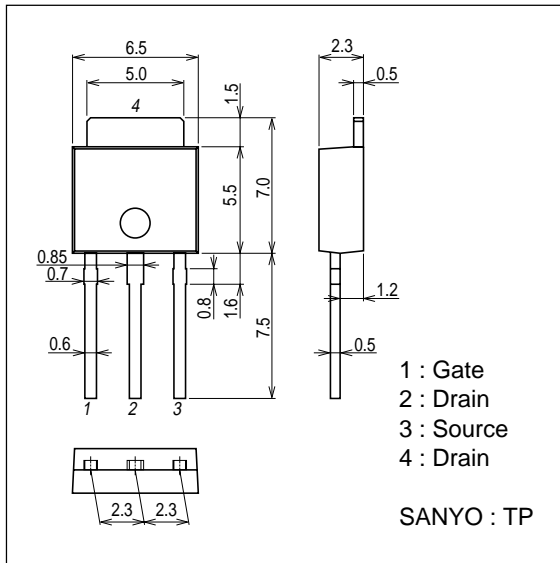
# 2SK4067

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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Turn-ON Delay Time	$t_d(\text{on})$	See specified Test Circuit.		9		ns
Rise Time	$t_r$	See specified Test Circuit.		8		ns
Turn-OFF Delay Time	$t_d(\text{off})$	See specified Test Circuit.		19		ns
Fall Time	$t_f$	See specified Test Circuit.		8		ns
Total Gate Charge	$Q_g$	$V_{DS}=10V, V_{GS}=10V, I_D=8A$		6		nC
Gate-to-Source Charge	$Q_{gs}$	$V_{DS}=10V, V_{GS}=10V, I_D=8A$		1.2		nC
Gate-to-Drain "Miller" Charge	$Q_{gd}$	$V_{DS}=10V, V_{GS}=10V, I_D=8A$		1.0		nC
Diode Forward Voltage	$V_{SD}$	$I_S=8A, V_{GS}=0V$	1.05	1.2		V

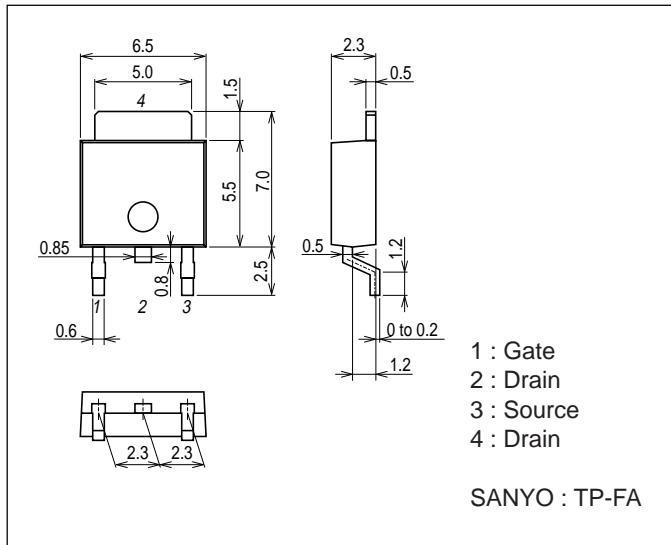
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unit : mm (typ)  
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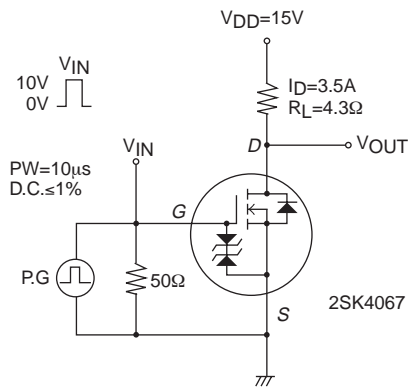


## Package Dimensions

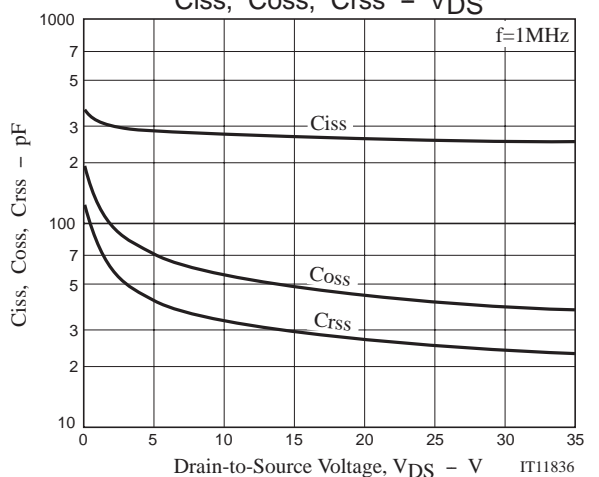
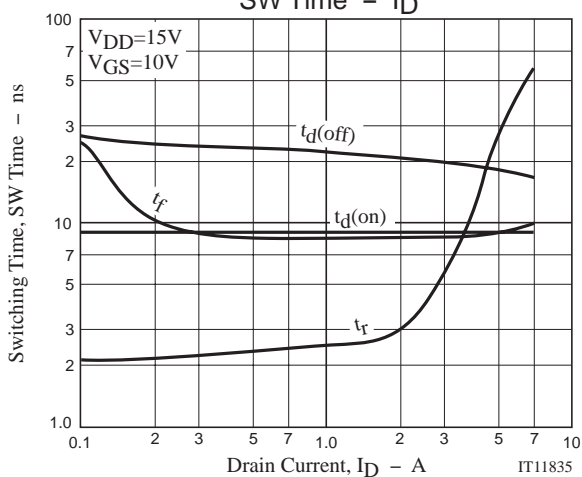
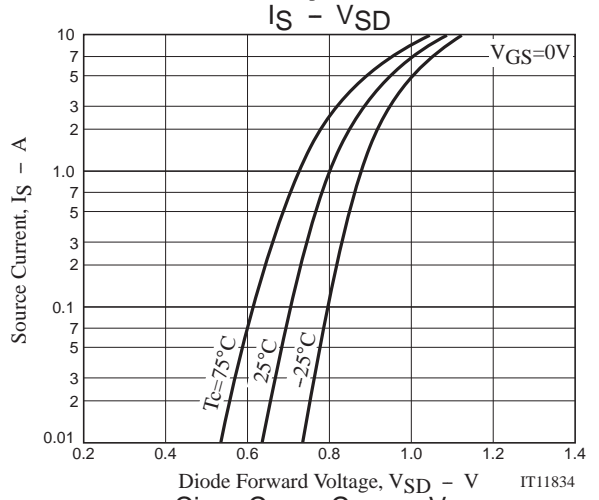
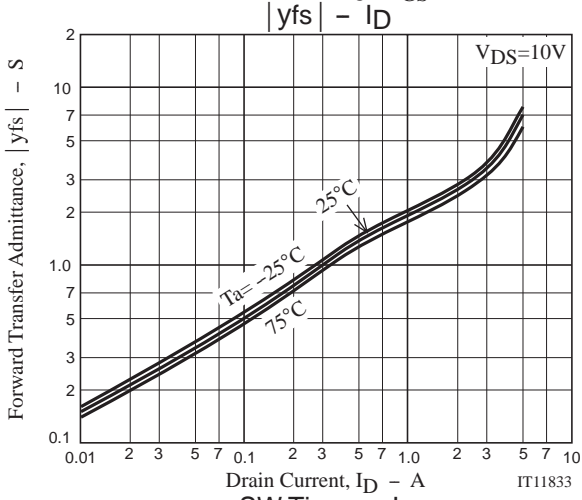
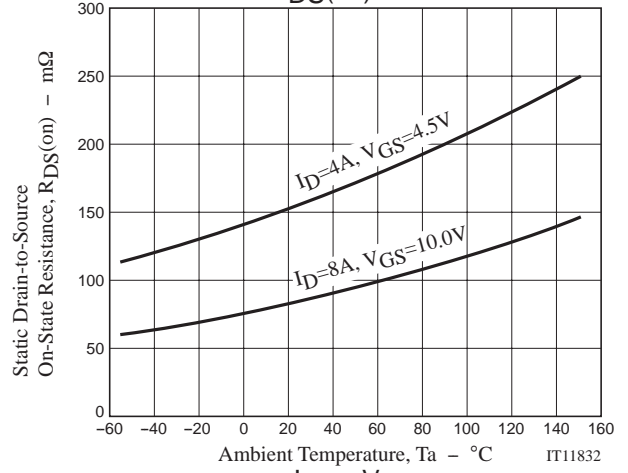
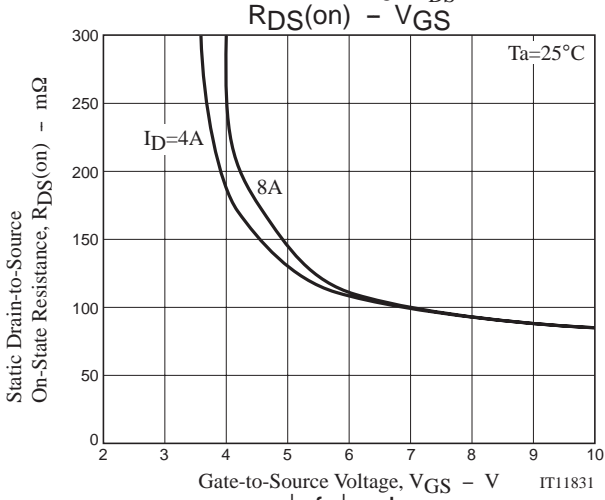
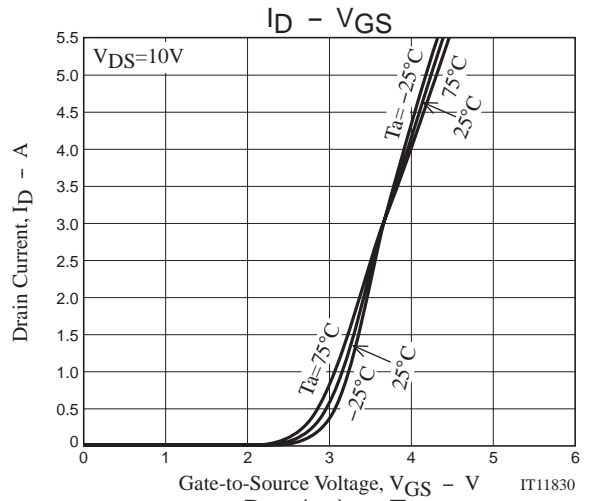
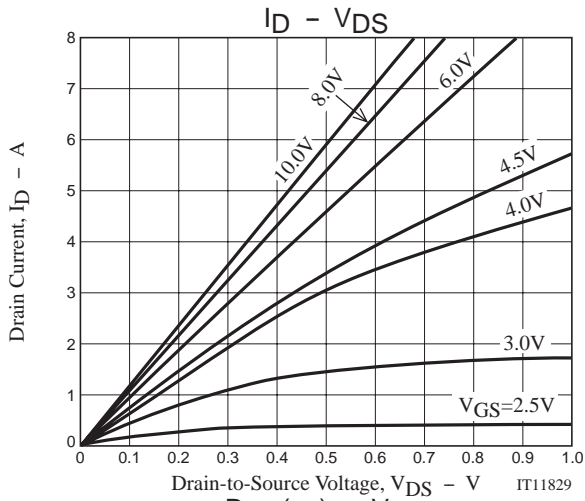
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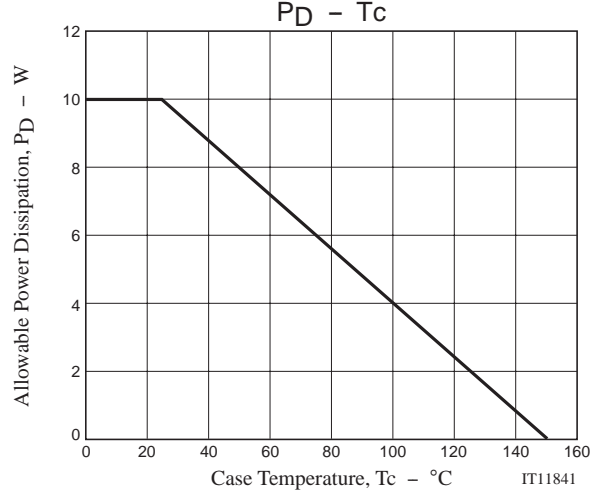
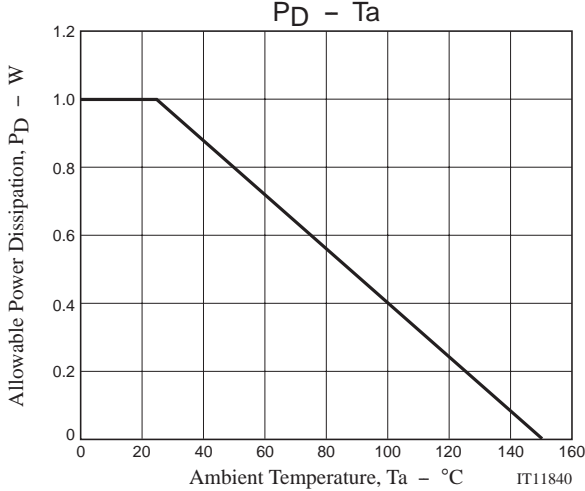
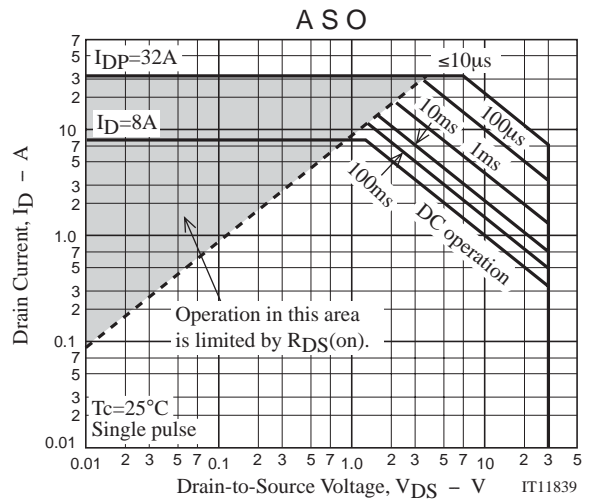
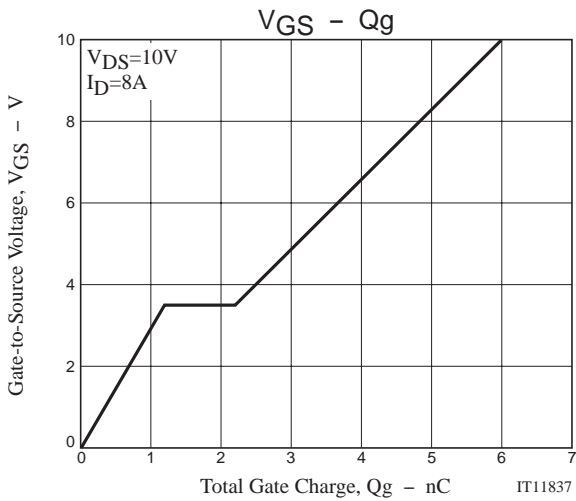


## Switching Time Test Circuit



# 2SK4067





Note on usage : Since the 2SK4067 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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